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August 2011

# FGA90N33ATD 330V, 90A PDP Trench IGBT

## **Features**

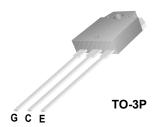
- · High current capability
- Low saturation voltage:  $V_{CE(sat)} = 1.1V @ I_C = 20A$
- · High input impedance
- · Fast switching
- · RoHS compliant

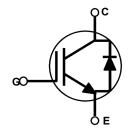
# **Applications**

· PDP System

# **General Description**

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.





# **Absolute Maximum Ratings**

Symbol	Description		Ratings	Units	
V <sub>CES</sub>	Collector to Emitter Voltage		330	V	
V <sub>GES</sub>	Gate to Emitter Voltage		± 30	V	
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	90	Α	
I <sub>C pulse(1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	220	А	
I <sub>C pulse(2)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	330	А	
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	223	W	
' D	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	89	W	
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.56	°C/W
$R_{\theta JC}(Diode)$	de) Thermal Resistance, Junction to Case		1.16	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

(1) Repetitive test , Pulse width=100usec , Duty=0.1 (2) Half sine wave , D<0.01, Pulse width<5usec \*I<sub>C</sub> pluse limited by max Tj

# **Package Marking and Ordering Information**

			Packaging		Max Qty	
Device Marking	Device	Package	Type	Qty per Tube	per Box	
FGA90N33ATD	FGA90N33ATDTU	TO-3P	Tube	30ea	-	

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 400\mu A$	330	-	-	V
I <sub>CES</sub>	Collector Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	-	-	400	μА
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C} = 250 \mu A, V_{CE} = V_{GE}$	2.5	4.0	5.5	V
()		I <sub>C</sub> = 20A, V <sub>GE</sub> = 15V	-	1.1	1.4	V
V	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 45A, V <sub>GE</sub> = 15V,	-	1.3	-	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation voltage	I <sub>C</sub> = 90A, V <sub>GE</sub> = 15V,	-	1.6	-	V
		I <sub>C</sub> = 90A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C	-	1.7	-	V
Dynamic C	haracteristics					
C <sub>ies</sub>	Input Capacitance		-	2200	-	pF
C <sub>oes</sub>	Output Capacitance	V <sub>CE</sub> = 30V <sub>,</sub> V <sub>GE</sub> = 0V, f = 1MHz	-	135	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 - 11VII 12	-	100	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	23	-	ns
t <sub>r</sub>	Rise Time	$V_{CC} = 200V, I_{C} = 20A,$	-	40	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$R_G = 5\Omega$ , $V_{GE} = 15V$ , Resistive Load, $T_C = 25^{\circ}C$	-	100	-	ns
t <sub>f</sub>	Fall Time		-	180	240	ns
t <sub>d(on)</sub>	Turn-On Delay Time		-	20	-	ns
t <sub>r</sub>	Rise Time	$V_{CC} = 200V, I_{C} = 20A,$ $R_{G} = 5\Omega, V_{GE} = 15V,$	-	40	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	Resistive Load, $T_C = 125^{\circ}C$	-	110	-	ns
t <sub>f</sub>	Fall Time		-	250	300	ns
Qg	Total Gate Charge		-	95	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	$V_{CE} = 200V, I_{C} = 20A,$ $V_{GE} = 15V$	-	12	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	▼GE - 13V	-	40	-	nC

# Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	าร	Min.	Тур.	Max	Units
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 10A	T <sub>C</sub> = 25°C	-	1.1	1.5	V
FIVI	Diode i Si ward Voltage	1F 10/1	T <sub>C</sub> = 125°C	-	0.96	-	]
t <sub>rr</sub>	Diode Reverse Recovery Time		$T_C = 25^{\circ}C$	-	23	-	ns
41	dr Biode Neverse Necestry Time		T <sub>C</sub> = 125°C	-	36	-	
Irr	Diode Peak Reverse Recovery	I <sub>F</sub> =10A, dI/dt = 200A/μs	T <sub>C</sub> = 25°C	-	2.8	-	Α
""	Current		T <sub>C</sub> = 125°C	-	5.1	-	]
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>C</sub> = 25°C	-	32	-	nC
~II	2.535 No. 5. 5. No. 50 No. 19		T <sub>C</sub> = 125°C	-	91	-	

**Figure 1. Typical Output Characteristics** 

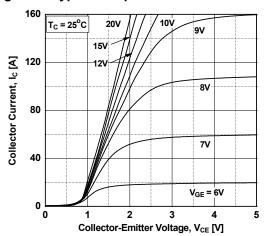


Figure 3. Typical Saturation Voltage Characteristics

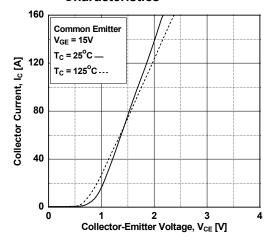
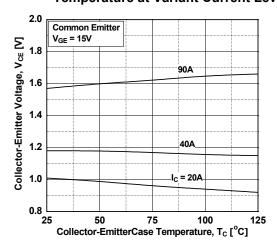


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 

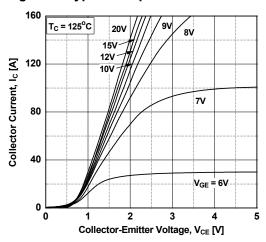


Figure 4. Transfer Characteristics

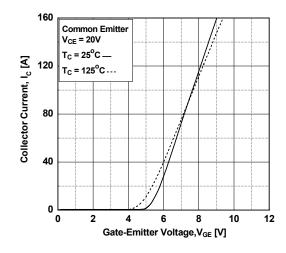


Figure 6. Saturation Voltage vs.  $V_{\text{GE}}$ 

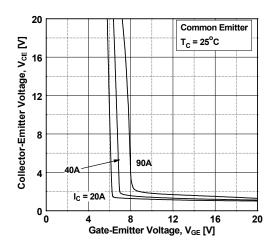


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

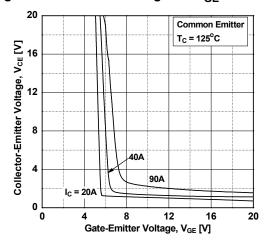


Figure 9. Gate charge Characteristics

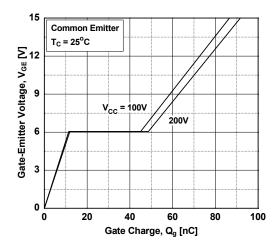
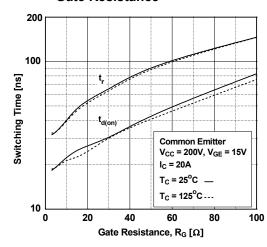


Figure 11. Turn-on Characteristics vs.
Gate Resistance



**Figure 8. Capacitance Characteristics** 

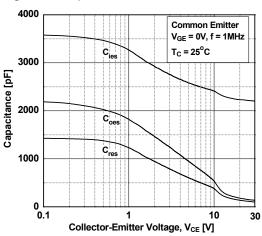


Figure 10. SOA Characteristics

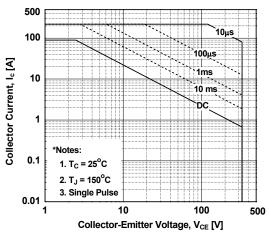


Figure 12. Turn-off Characteristics vs.
Gate Resistance

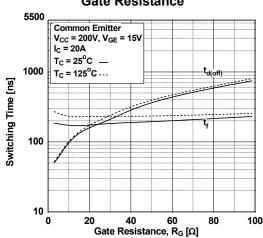


Figure 13. Turn-on Characteristics vs. Collector Current

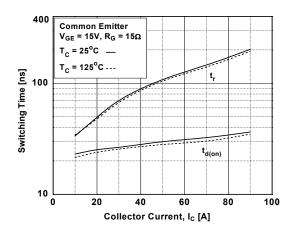


Figure 14. Turn-off Characteristics vs. Collector Current

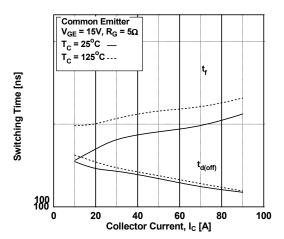
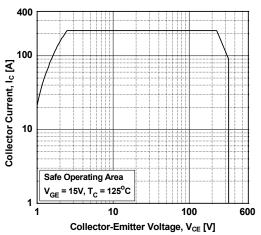


Figure 15. Turn off Switching SOA Characteristics Figure 16. Forward Characteristics



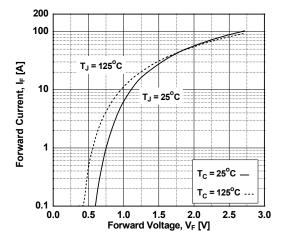


Figure 17. Reverse Recovery Current

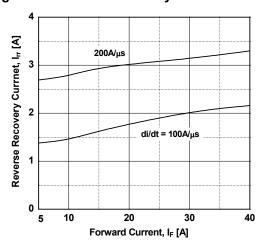


Figure 18. Stored Charge

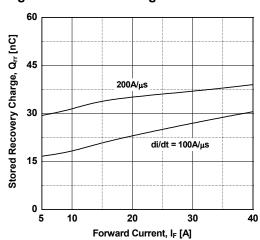
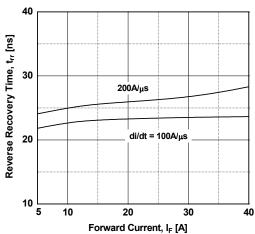
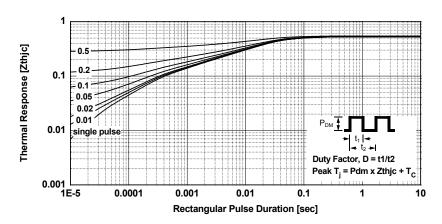


Figure 19. Reverse Recovery Current

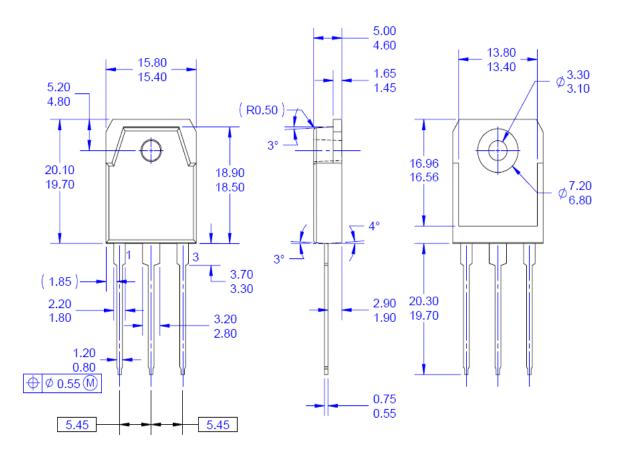






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## TO-3PN





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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
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